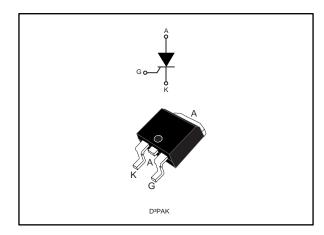


TN2010H-6G

High temperature 20 A SCRs

Datasheet - production data



Features

- High junction temperature: T_i = 150 °C
- High noise immunity $dV/dt = 400 V/\mu s$ up to 150 °C
- Gate triggering current I_{GT} = 10 mA
- Peak off-state voltage V_{DRM}/V_{RRM} = 600 V
- High turn on current rise dl/dt = 100 A/μs
- ECOPACK®2 compliant component

Applications

- Motorbike voltage regulator circuits
- Inrush current limiting circuits
- Motor control circuits and starters
- Light dimmers
- Solid state relays

Description

This device offers high thermal performance during operation of up to 20 A_{RMS}, thanks to a junction temperature of up to 150 °C.

Its D²PAK package allows modern SMD designs as well as compact back to back configuration.

The combination of noise immunity and low gate triggering current allows to design strong and compact control circuits.

Table 1: Device summary

Order code	Package	V _{DRM} /V _{RRM}	Іст
TN2010H-6G	D²PAK	600 V	10 mA

Characteristics TN2010H-6G

1 Characteristics

Table 2: Absolute maximum ratings (limiting values), $T_j = 25$ °C unless otherwise specified

Symbol	Parame	Value	Unit			
I _{T(RMS)}	RMS on-state current (180 ° conduction angle)	T _c = 132 °C	20	Α		
			T _c = 132 °C	12.7		
I _{T(AV)}	Average on-state current (180 ° conduction angle)		T _c = 137 °C	10	Α	
	(100 conduction angle)		T _c = 140 °C	8		
	Non repetitive surge peak on-state	current	$t_p = 8.3 \text{ ms}$	197		
Ітѕм	$(T_j \text{ initial} = 25 °C)$		$t_p = 10 \text{ ms}$	180	Α	
l ² t	I ² t value for fusing	t _p = 10 ms	162	A ² s		
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, tr $\leq 100 \text{ ns}$ $f = 60 \text{ H}$		f = 60 Hz	100	A/µs	
V _{DSM} /V _{RSM}	Non repetitive surge peak off-state	voltage	$t_p = 10 \text{ ms}$	700	V	
l _{GM}	Peak gate current	t _p = 20 μs	T _j = 150 °C	4	Α	
P _{G(AV)}	Average gate power dissipation $T_j = 150 \text{ °C}$			1	W	
V _{RGM}	Maximum peak reverse gate voltage			5	V	
T _{stg}	Storage junction temperature range			-40 to +150	°C	
Tj	Operating junction temperature range			-40 to +150	°C	

Table 3: Electrical characteristics ($T_j = 25$ °C unless otherwise specified)

Symbol	Test conditions	Value	Unit		
1			Тур.	5	A
l _{GT}	$V_D = 12 \text{ V}, R_L = 33 \Omega$		Max.	10	mA
V _{GT}			Max.	1.3	V
V_{GD}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$	T _j = 150 °C	Min.	0.1	V
lн	I _T = 500 mA, gate open	Max.	40	mA	
lμ	I _G = 1.2 x I _G T	Max.	60	mA	
dV/dt	$V_D = 402 \text{ V}$, gate open $T_j = 150 \text{ °C}$			400	V/µs
t _{gt}	$I_{TM} = 40 \text{ A}, V_D = 402 \text{ V}, I_G = 20 \text{ mA}, (dI_G/dt) \text{ max} = 0.2 \text{ A/}\mu\text{s}$			1.9	μs
tq	$I_{TM} = 40 \text{ A}, V_D = 402 \text{ V}, (d_I/dt) \text{off} = 30 \text{ A/}\mu\text{s}, V_R = 25 \text{ V}, dV_D/dt = 40 \text{ V/}\mu\text{s}$	Тур.	70	μs	

TN2010H-6G Characteristics

Table 4: Static characteristics

Symbol	Test conditions			Value	Unit
V_{TM}	$I_{TM} = 40 \text{ A}, t_p = 380 \mu\text{s}$	T _j = 25 °C	Max.	1.6	\/
V _{TO}	Threshold voltage	T _j = 150 °C	Max.	0.82	V
R _D	Dynamic resistance	T _j = 150 °C	Max.	17.5	mΩ
		T _j = 25 °C		5	μΑ
I _{DRM} , I _{RRM}	$V_D = V_{DRM}, V_R = V_{RRM}$	T _j = 125 °C	Max.	2	^
		T _j = 150 °C		3.9	mA

Table 5: Thermal parameters

Symbol	Parameter			Value	Unit
R _{th(j-c)}	Junction to case (DC)		Max.	1.0	0000
R _{th(j-a)}	Junction to ambient (DC) $S^{(1)} = 2.5 \text{ cm}2$		Тур.	45	°C/W

Notes:

⁽¹⁾S = Copper surface under tab

Characteristics TN2010H-6G

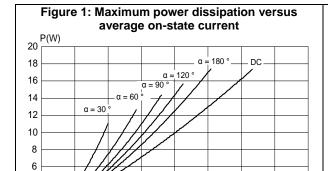
 $I_{T(AV)}(A)$

15

1.1 Characteristics (curves)

4

2



10

Figure 2: Average and DC on-state current versus case temperature $I_{T(AV)}(A)$ 24 DC 22 20 18 16 14 12 α = 120 10 α = 90 ° — 8 α = 30 ° 6 4 2 T_c(°C) 0 6 75

Figure 4: Relative variation of thermal impedance versus pulse duration

K = [Z_{th}/ R_{th}]

1.0E+00

7.th(j-c)

1.0E-01

1.0E-02

1.0E-03

1.0E-02

1.0E-03

1.0E-01

1.0E+00

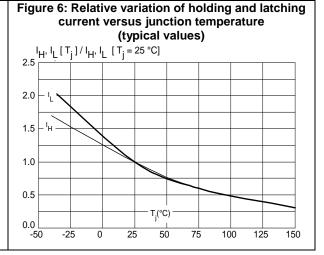
1.0E+00

1.0E+01

1.0E+02

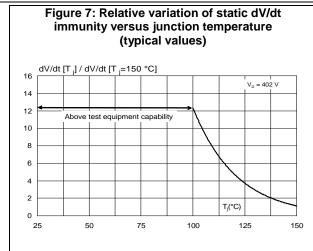
1.0E+03

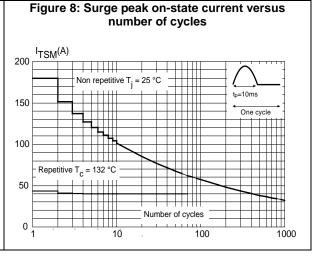
Figure 5: Relative variation of gate triggering current and gate voltage versus junction temperature (typical values) I_{GT} , V_{GT} [T_i] / I_{GT} , V_{GT} [T_i = 25 °C] 1.5 1.0 0.5 T_i(°C) 0.0 -25 -50 25 50 75 100 125 150

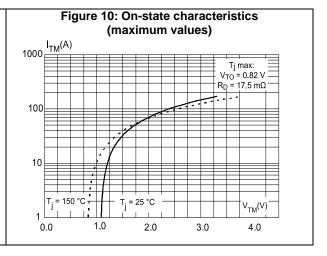


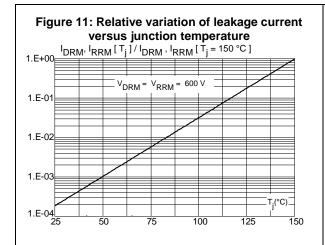
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TN2010H-6G Characteristics









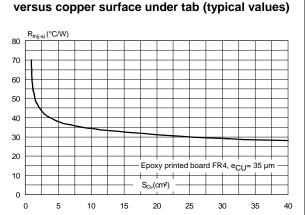


Figure 12: Thermal resistance junction to ambient

Package information TN2010H-6G

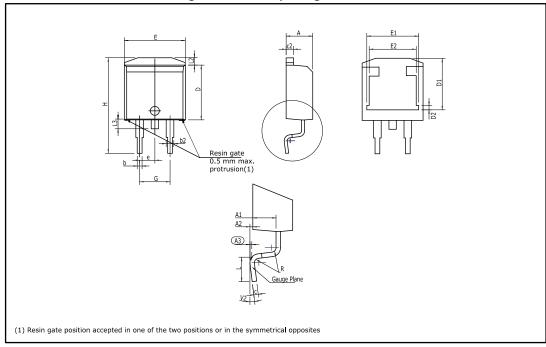
2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Lead-free, halogen-free package

2.1 D²PAK package information

Figure 13: D²PAK package outline



TN2010H-6G Package information

Table 6: D²PAK package mechanical data

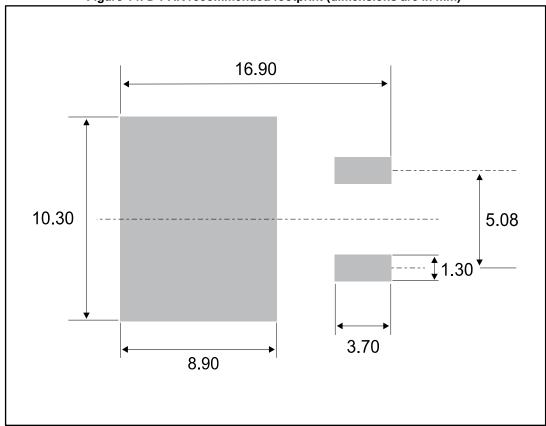
	Dimensions					
Ref.		Millimeters		Inches ⁽¹⁾		
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	4.30		4.60	0.1693		0.1811
A1	2.49		2.69	0.0980		0.1059
A2	0.03		0.23	0.0012		0.0091
A3		0.25			0.0098	
b	0.70		0.93	0.0276		0.0366
b2	1.25		1.7	0.0492		0.0669
С	0.45		0.60	0.0177		0.0236
c2	1.21		1.36	0.0476		0.0535
D	8.95		9.35	0.3524		0.3681
D1	7.50		8.00	0.2953		0.3150
D2	1.30		1.70	0.0512		0.0669
е	2.54			0.1		
Е	10.00		10.28	0.3937		0.4047
E1	8.30		8.70	0.3268		0.3425
E2	6.85		7.25	0.2697		0.2854
G	4.88		5.28	0.1921		0.2079
Н	15		15.85	0.5906		0.6240
L	1.78		2.28	0.0701		0.0898
L2	1.27		1.40	0.0500		0.0551
L3	1.40		1.75	0.0551		0.0689
R		0.40			0.0157	
V2	0°		8°	0°		8°

Notes:

 $^{^{(1)}\}mbox{Dimensions}$ in inches are given for reference only

Package information TN2010H-6G

Figure 14: D²PAK recommended footprint (dimensions are in mm)



TN2010H-6G Ordering information

3 Ordering information

Figure 15: Ordering information scheme

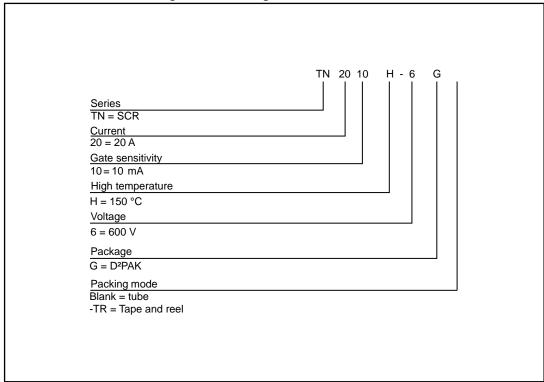


Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN2010H-6G	TNOOLOUG	D2DAI/	2.2 ~	50	Tube
TN2010H-6G-TR	TN2010H6	D²PAK	2.3 g	1000	Tape and reel

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
24-Aug-2017	1	Initial release.

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